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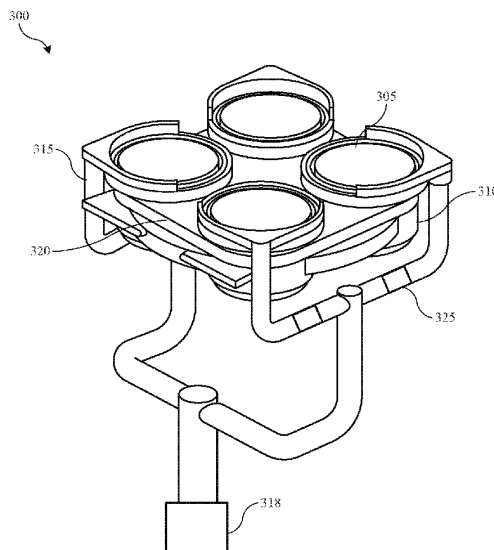


FIG. 3

(57) Abstract: Exemplary methods of semiconductor processing may include flowing a silicon-containing precursor into a processing region of a semiconductor processing chamber. A substrate may be housed within the processing region, and the substrate may be maintained at a temperature below or about 450 °C. The methods may include striking a plasma of the silicon-containing precursor. The methods may include forming a layer of amorphous silicon on a semiconductor substrate. The layer of amorphous silicon may be characterized by less than or about 3% hydrogen incorporation.

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